



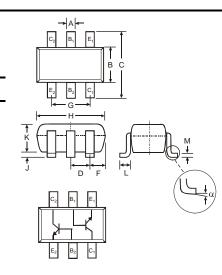
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### Features

- **Epitaxial Planar Die Construction** .
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)

### **Mechanical Data**

- Case: SOT-363 •
- Case Material: Molded Plastic. UL Flammability • Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C .
- Terminals: Solderable per MIL-STD-202, Method 208 .
- Lead Free Plating (Matte Tin Finish annealed over • Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



SOT-363									
Dim	Min	Max							
Α	0.10	0.30							
В	1.15	1.35							
С	2.00 2.20								
D	0.65 N	0.65 Nominal							
F	0.30	0.40							
н	1.80	2.20							
J		0.10							
к	0.90 1.00								
L	0.25	0.40							
М	0.10	0.25							
α	0°	8°							
All Dir	All Dimensions in mm								

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current - Continuous	lc	200	mA
Power Dissipation (Note 1)	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient	R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>i</sub> , T <sub>STG</sub>	-55 to +150	°C

1. Device mounted on FR-4 PCB; pad layout as shown on Diodes Inc. suggested pad layout documents APO2001, Notes: which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

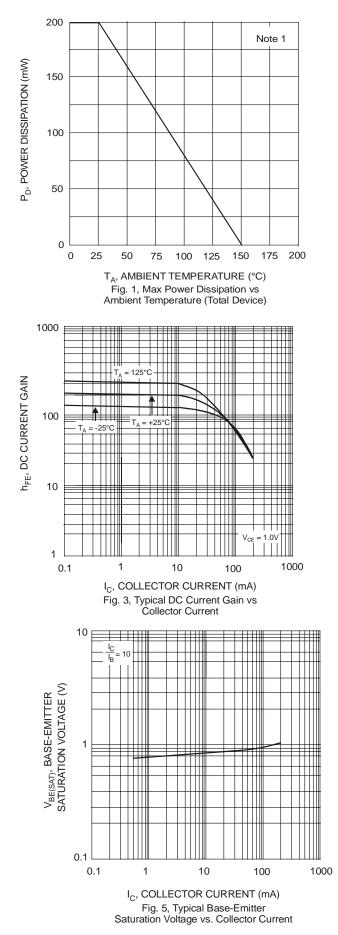
2. No purposefully added lead.

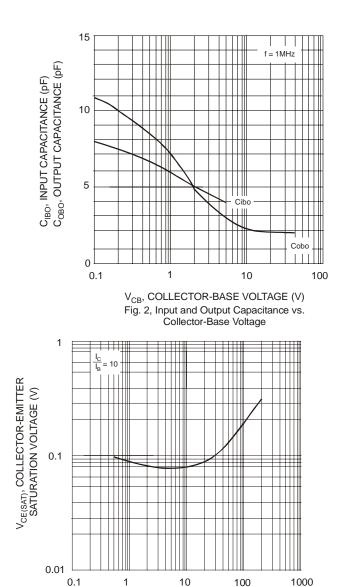


Electrical Characteristics @T <sub>A</sub> = 25°C unless otherwise specified									
Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 3)			·		•				
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	60	_	V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$				
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	_	V	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0$				
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5.0	_	V	$I_{E} = 10 \mu A, I_{C} = 0$				
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$				
Base Cutoff Current	I <sub>BL</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$				
ON CHARACTERISTICS (Note 3)			•		-				
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	 300 	_	$ \begin{array}{ll} I_{C} = & 100 \mu A, \ V_{CE} = & 1.0 V \\ I_{C} = & 1.0 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 10 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 50 m A, \ V_{CE} = & 1.0 V \\ I_{C} = & 100 m A, \ V_{CE} = & 1.0 V \\ \end{array} $				
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.20 0.30	V	$\begin{split} I_{C} &= 10 \text{mA}, \ I_{B} = 1.0 \text{mA} \\ I_{C} &= 50 \text{mA}, \ I_{B} = 5.0 \text{mA} \end{split}$				
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	V	$\begin{split} I_{C} &= 10 mA, \ I_{B} = 1.0 mA \\ I_{C} &= 50 mA, \ I_{B} = 5.0 mA \end{split}$				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	C <sub>obo</sub>	_	4.0	pF	$V_{CB} = 5.0V, f = 1.0MHz, I_E = 0$				
nput Capacitance	C <sub>ibo</sub>	_	8.0	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$				
nput Impedance	h <sub>ie</sub>	1.0	10	kΩ					
/oltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$				
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz				
Output Admittance	h <sub>oe</sub>	1.0	40	μS					
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_C = 10mA,$ f = 100MHz				
Noise Figure	NF		5.0	dB	$V_{CE} = 5.0V, I_C = 100\mu A, R_S = 1.0k\Omega, f = 1.0kHz$				
SWITCHING CHARACTERISTICS	· · · · ·								
Delay Time	t <sub>d</sub>	—	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$				
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$				
Storage Time	t <sub>s</sub>	_	200	ns	$V_{CC} = 3.0V, I_C = 10mA,$				
Fall Time	t <sub>f</sub>	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$				

Notes: 3. Short duration pulse test used to minimize self-heating.







I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current



## Ordering Information (Note 4)

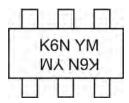
Device	Packaging	Shipping			
MMDT3904-7-F	SOT-363	3000/Tape & Reel			

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

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# Marking Information



K6N = Product Type Marking Code YM = Date Code Marking Y = Year ex: N = 2002 M = Month ex: 9 = September

Data Code Key

Code

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	к	L	М	Ν	Р	R	S	Т	U	V	W	Х	Y	Z
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Month	Jan	Feb	o I	Mar	Apr	Мау	Ju	n	Jul	Aug	Sep	Oc	t M	lov	Dec

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